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November 2013

FQB9P25

P-Channel QFET® MOSFET

-250 V, -9.4 A, 620 mΩ

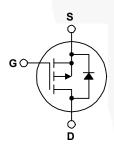
Description

These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology is especially tailored to minimize on-state resistance, provide superior switching performance, and withstand a high energy pulse in the avalanche and commutation modes. These devices are well suited for high efficiency switching DC/DC converters.

Features

- -9.4 A, -250 V, $R_{DS(on)}$ = 620 m Ω (Max.) @ V_{GS} = -10 V, I_D = -4.7 A
- Low Gate Charge (Typ. 29 nC)
- · Low Crss (Typ. 27 pF)
- · 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQB9P25TM	Unit
V_{DSS}	Drain-Source Voltage		-250	V
I _D	Drain Current - Continuous (T _C = 25°	C)	-9.4	Α
	- Continuous (T _C = 100°C)		-5.9	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	-37.6	Α
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	650	mJ
I _{AR}	Avalanche Current	(Note 1)	-9.4	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	12	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		-5.5	V/ns
P _D	Power Dissipation (T _A = 25°C) *		3.13	W
	Power Dissipation (T _C = 25°C)		120	W
	- Derate above 25°C		0.96	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQB9P25TM	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 1.04			
Б	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40		

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQB9P25TM	FQB9P25	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	racteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-250			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-0.2		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -250 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
		V _{DS} = -200 V, T _C = 125°C			-10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-3.0		-5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -4.7 A		0.48	0.62	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = -40 \text{ V}, I_{D} = -4.7 \text{ A}$		5.7		S
C _{iss}	Input Capacitance Output Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$		910 170	1180 220	pF pF
C _{oss}	Output Capacitance	f = 1.0 MHz		170	220	pF
C _{rss}	Reverse Transfer Capacitance			27	35	pF
Switchi	ng Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = -125 V, I _D = -9.4 A,		20	50	ns
t _r	Turn-On Rise Time	$R_{G} = 25 \Omega$		150	310	ns
t _{d(off)}	Turn-Off Delay Time	- · · · · · · · · · · · · · · · · · · ·		45	100	ns
t _f	Turn-Off Fall Time	(Note 4)		65	140	ns
Q_g	Total Gate Charge	$V_{DS} = -200 \text{ V}, I_{D} = -9.4 \text{ A},$		29	38	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V	/	7.6		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		14		nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				-9.4	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				-37.6	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -9.4 \text{ A}$			-5.0	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_S = -9.4 \text{ A},$		190	//	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		1.45		μС

Notes:

- Notes. 1. Repetitive rating: pulse-width limited by maximum junction temperature. 2. L = 11.8 mH, I_{AS} = -9.4 A, V_{DD} = -50 V, R_{G} = 25 Ω , starting T_{J} = 25°C. 3. I_{SD} ≤ -9.4 A, di/dt ≤ 300 A/ μ s, V_{DD} ≤ BV $_{DSS}$, starting T_{J} = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

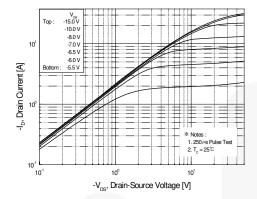


Figure 1. On-Region Characteristics

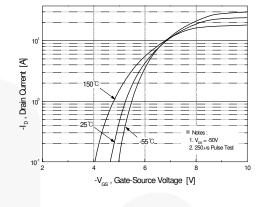


Figure 2. Transfer Characteristics

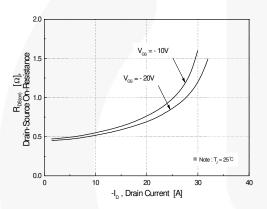


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

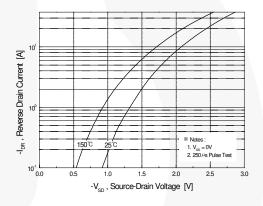


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

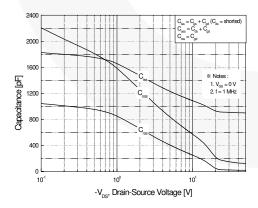


Figure 5. Capacitance Characteristics

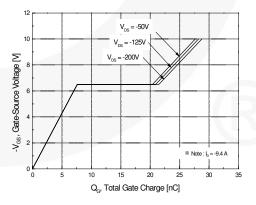


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

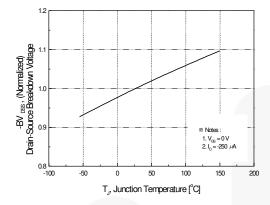


Figure 7. Breakdown Voltage Variation vs. Temperature

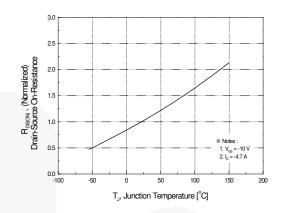


Figure 8. On-Resistance Variation vs. Temperature

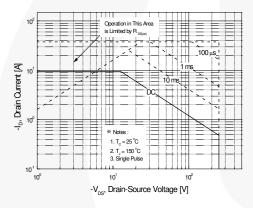


Figure 9. Maximum Safe Operating Area

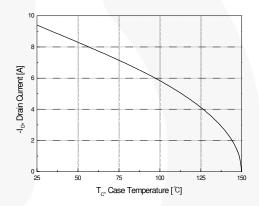


Figure 10. Maximum Drain Current vs. Case Temperature

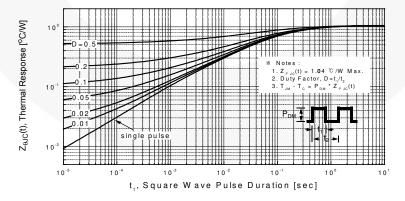


Figure 11. Transient Thermal Response Curve

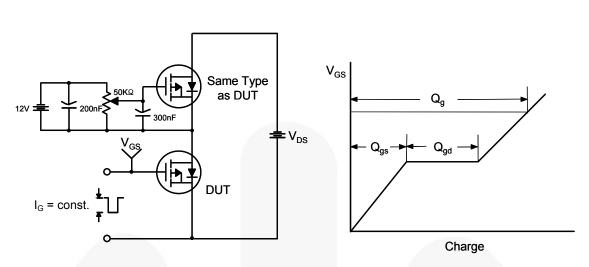


Figure 12. Gate Charge Test Circuit & Waveform

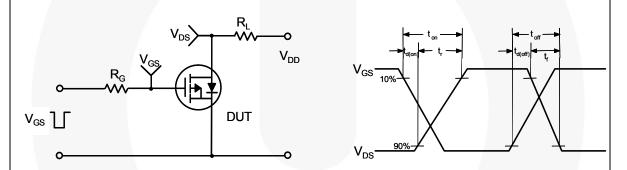


Figure 13. Resistive Switching Test Circuit & Waveforms

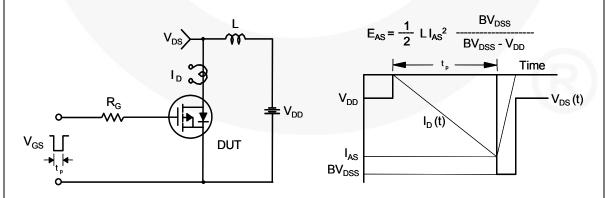
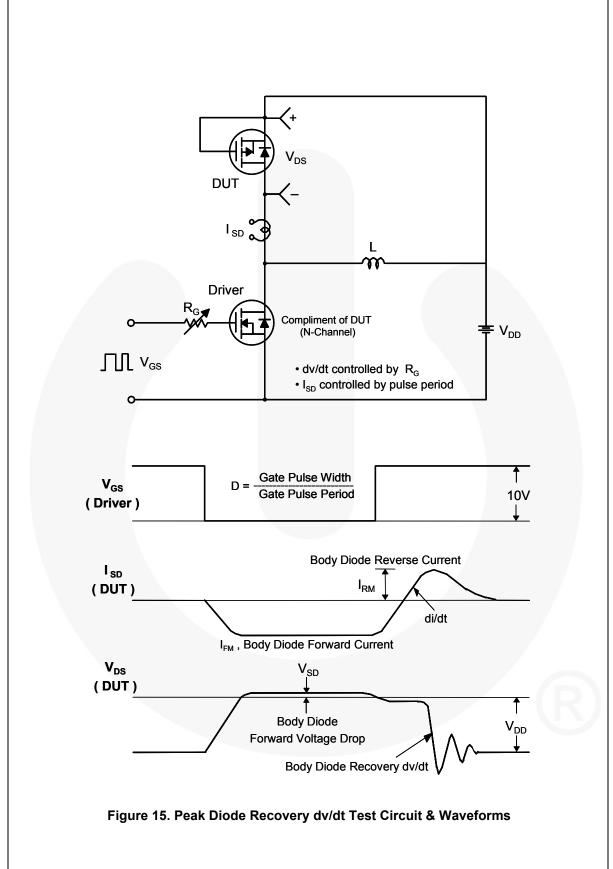


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

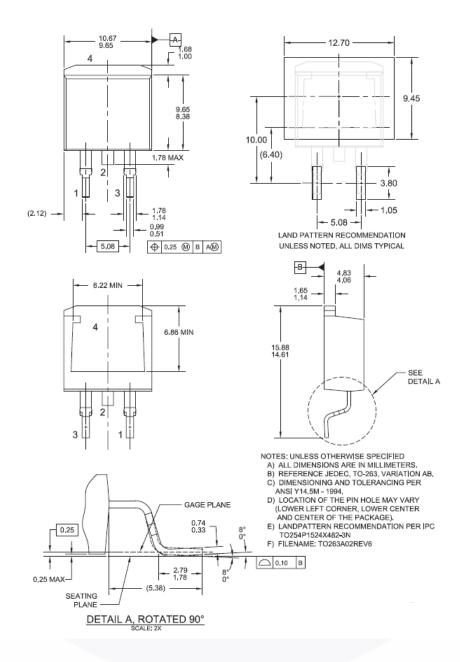


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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